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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)

Applicant	
Douglas D.	COOLBAUGH

Filing Date January 23, 2004

Group 2811

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FOREIGN PATENT DOCUMENTS

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SPE	4	-	0	6	2	9	7	7	02/27/92	JAPAN				
200	63	-	3	0	0	5	7	0	12/07/88	JAPAN				
SKI	2003	-	3	-/	8	4	1	4	11/07/03	JAPAN				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

U		Materials, Vol. 22, No. 1, 1993, pp. 03-10.
		Energy Si, S, and Si/S Implantation for Application to Microwave Devices", Journal of Electronic
	4	An Article of VELLANKI et al., entitled: "Highly Conductive n+ Layers in InP:Fe Created by MeV
	3	English Language Abstract of JP 1-019779.
1	2	English Language Abstract of JP 2003-318414.
SIL	1	English Language Abstract of JP 4-062977.

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